


| | | | |
|----------------------------------|----------------------|------------|----|
| Storage Temperature | T_{STG} | -55 to 150 | °C |
| Single Pulse Avalanche Energy | E_{AS} | 110 | mJ |
| Diode continuous forward current | $I_S@T_C=25^\circ C$ | 55 | A |

Thermal resistance

| Parameter | Symbol | Min. | Typ. | Max. | Unit |
|-------------------------------------|------------|------|------|------|------|
| Thermal resistance, junction - case | R_{thJC} | | — | | |



| | | | | | |
|----------------------|----------|------------------------------|---|---|---|
| Gate - Source charge | Q_{gs} | $I_D = 5A$ $V_{GS} = 10V$ | - | 4 | - |
| Gate - Drain charge | Q_{gd} | | - | 6 | - |

Turn-ON Delay time $t_{D(on)}$

$V_{GS}=10V, V_{DS}=15V$

$R_G = 3.$

Fig.5 On-Resistance VS Gate Source Voltage

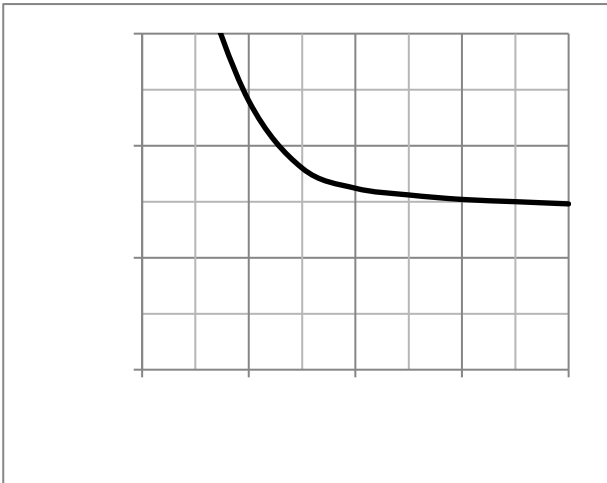


Fig.6 On-Resistance V.S Junction Temperature

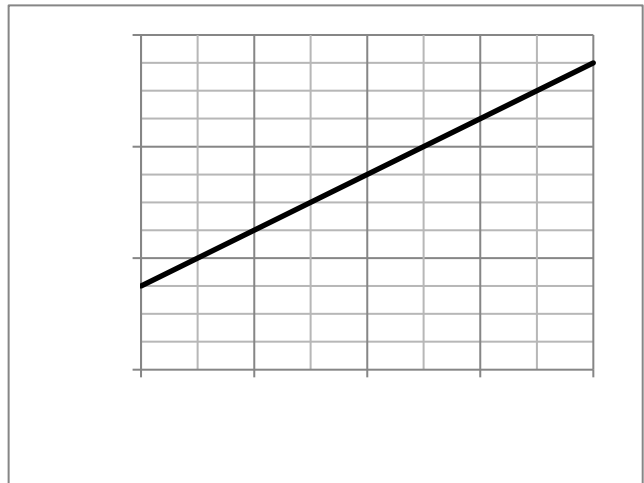


Fig.7 SOA Maximum Safe Operating Area

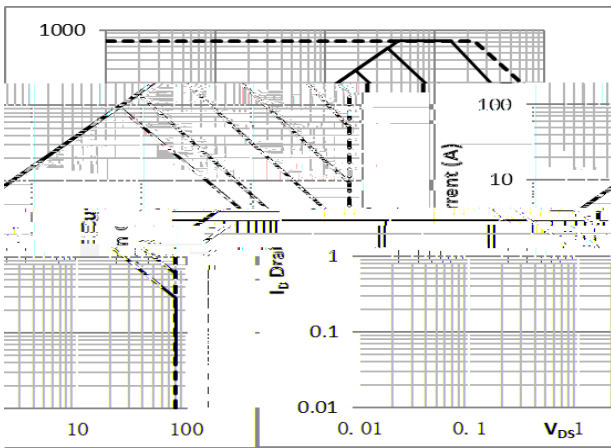


Figure 8. Diode Forward Voltage vs. Current

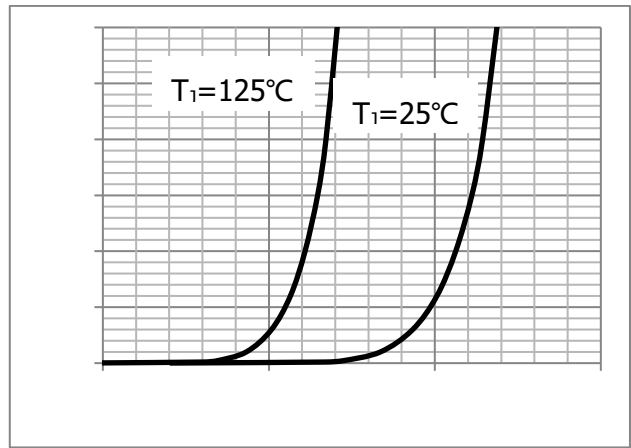


Figure 9. Transfer Characteristics

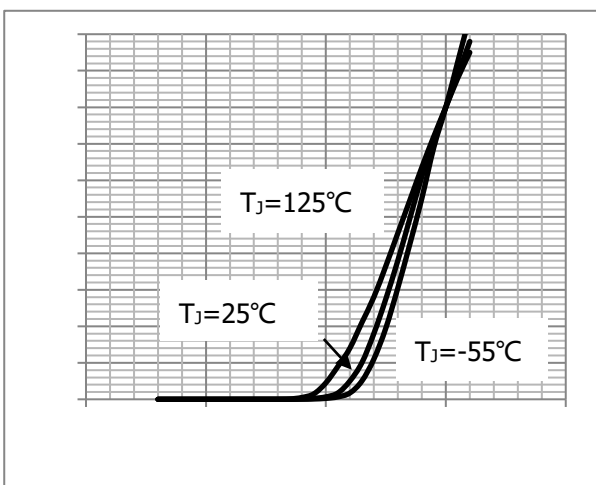


Fig.10 Typical output Characteristics

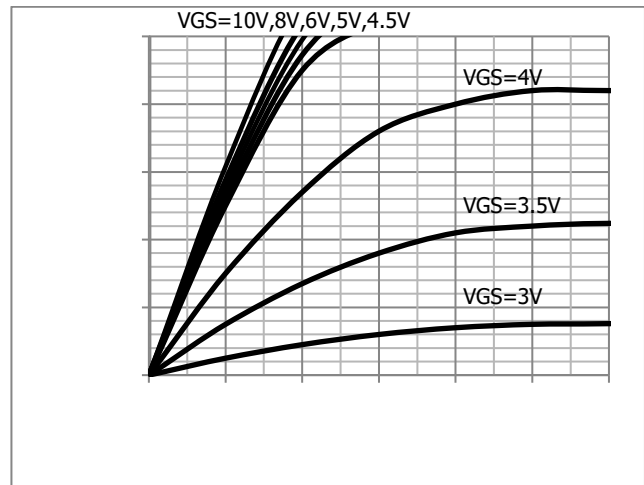
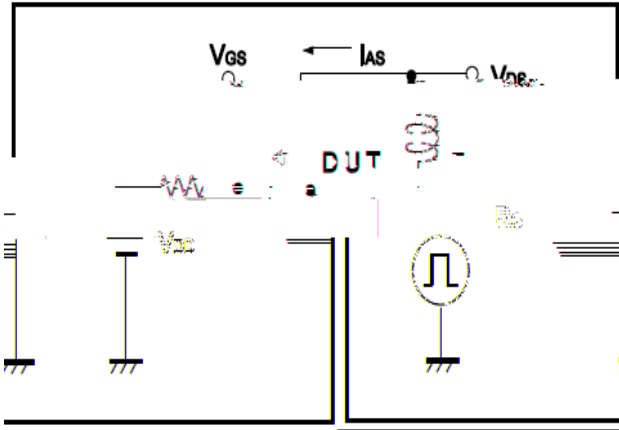




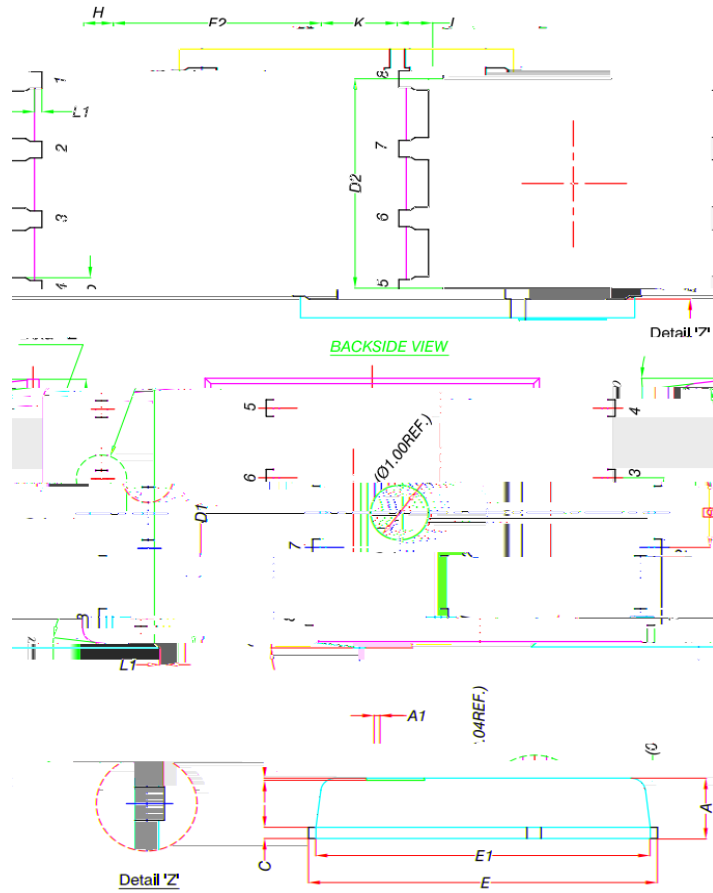
Fig.17 Avalanche Measurement Circuit





sions DFN5x6

Unit mm



| DIM. | MILLIMETERS | | |
|------|-------------|------|------|
| | MIN. | NOM. | MAX. |
| A | 0.90 | 1.00 | 1.10 |
| A1 | 0 | - | 0.05 |
| b | 0.33 | 0.41 | 0.51 |
| C | 0.20 | 0.25 | 0.30 |
| D1 | 4.80 | 4.90 | 5.00 |
| D2 | 3.61 | 3.81 | 3.96 |

| | | | | |
|----|----------|------|------|---|
| 1 | 5.70 | 5.75 | 5.80 | E |
| E2 | 3.38 | 3.58 | 3.78 | |
| e | 1.27 BSC | | | |
| H | 0.41 | 0.51 | 0.61 | |
| K | 1.10 | | | |
| L1 | 0.31 | 0.51 | 0.61 | |
| L2 | 0.20 | 0.06 | 0.1 | |